Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	702/132.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:05
L2	0	324/755.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 13:06
L3	. 0	365/201.ccls.and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:07
L4		324/760.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 13:01
L5 	0	324/754.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:07
L6	0	324/765.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:07
L7	. 0	438/15.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:07

<u></u>			110 000::0	00	055	2006/40/25 42 25
L8	0	714/724.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:08
L9		324/755.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated with circuit or wafer) same (power or current) same (ambient same temperature) same body same voltage same bias\$3 same (junction same temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 13:05
L10	1	702/132.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated) same (circuit or wafer) same (power or current) same (ambient same temperature) same body same voltage same bias\$3 same (junction same temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:06
L11		324/755.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated) same (circuit or wafer) same (power or current) same (ambient same temperature) same body same voltage same bias\$3 same (junction same temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 13:06
L13	0	365/201.ccls.and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated) same (circuit or wafer) same (power or current) same (ambient same temperature) same body same voltage same bias\$3 same (junction same temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:07
L14	0	324/754.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated) same (circuit or wafer) same (power or current) same (ambient same temperature) same body same voltage same bias\$3 same (junction same temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:07
L15	. 0	324/765.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated) same (circuit or wafer) same (power or current) same (ambient same temperature) same body same voltage same bias\$3 same (junction same temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:07
L16	0	438/15.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated) same (circuit or wafer) same (power or current) same (ambient same temperature) same body same voltage same bias\$3 same (junction same temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:07

L17	0	714/724.ccls. and ((determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated) same (circuit or wafer) same (power or current) same (ambient same temperature) same body same voltage same bias\$3 same (junction same temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:08
S1	176 _.	702/132.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 12:58
S2	75	702/131.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:45
S3	633	702/130.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:45
S4	433	702/64.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:46
S5	116993	temperature and (integrat\$2 or IC) and test	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 10:54
S6	24	S1 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:51
S7	5	S2 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:50
S8	93	S3 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:50
S9	49	S4 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:50

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S10	4023	temperature same (integrat\$2 or IC) same test	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:50
S11	8	S1 and S10	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:52
S12	0	S2 and S10	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:52
S13	18	S3 and S10	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:51
S14	4	S4 and S10	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:51
S15	166	S10 and "702"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:58
S16	2	"20040183588"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:00
S17	. 1	"20050088137"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 11:59
S18	431	327/545.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:00
S19	0	S18 and S10	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:01
S20	402	318/806.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:01

S21	8	S18 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:01
S22	12	S20 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR .	OFF	2005/05/24 12:08
S23	21091	((voltage or power or current) with control\$4) and (((semiconductor with substrate) or (integrated adj circuit\$1) or wafer\$1 or chip\$1) with temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:46
S24	4104	S23 and ((environmental or ambient) near5 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR .	OFF	2005/05/24 13:47
S25	688	S24 and (voltage near3 bias\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:17
S26	78	S25 and (thermal near4 resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR ·	OFF	2005/05/24 12:16
S27	495	S25 and ((power or voltage) near4 supply)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:19
S28	241	S25 and ((power or voltage) near4 supply with temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:20
S29	228	S28 and (current with voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 12:20
S30	37	702/129.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR .	OFF	2005/05/24 13:44
S31	1	S30 and (temperature and (integrat\$2 or IC) and test)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:46

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S32	4207	324/765.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR ·	OFF	2005/05/24 13:46
S33	821	S32 and (temperature and (integrat\$2 or IC) and test)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:46
S34	192	S32 and (((voltage or power or current) with control\$4) and (((semiconductor with substrate) or (integrated adj circuit\$1) or wafer\$1 or chip\$1) with temperature))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:46
S35	36	S34 and ((environmental or ambient) near5 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:47
S36	21091	((voltage or power or current) with control\$4) and (((semiconductor with substrate) or (integrated adj circuit\$1) or wafer\$1 or chip\$1) with temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:48
S37	4104	S36 and ((environmental or ambient) near5 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:48
S38	688	S37 and (voltage near3 bias\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF .	2005/11/10 15:32
S39	241	S38 and ((power or voltage) near4 supply with temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:48
S40	228	S39 and (current with voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/05/24 13:48
S41	39	S40 and (junction near5 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/05/16 14:51
S42	14662	(junction near5 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 15:31

S43	1864	body near5 voltage near5 bias\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/10 15:36
S44	18	S42 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/10 15:32
S45	75	body near5 voltage near5 bias\$3 with temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/10 16:06
S46	78	body near5 voltage near5 bias\$3 with temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR .	ON	2005/11/10 15:36
S47	83	body near5 voltage near5 bias\$3 with (temperature or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 15:37
S48	136	body near5 voltage near5 bias\$3 same (temperature or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR .	ON	2005/11/10 16:07
S49	38	body near5 voltage near5 bias\$3 same (regulat\$3 or desired or optimaliz\$3 or stabliz\$3 or control\$4 or maintain\$3 or management or optimum) near5 (temperature or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/24 09:34
S50	6	S49 and junction with temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/10 16:04
S51	2	"6100751".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR .	ON	2005/11/11 09:52
S53	2020	(measur\$5 or determin\$3 or obtain\$3 or calculat\$3 or estimat\$3 or monitor\$3) with (power near4 consum\$5) with (die or chip or IC or integrated adj circuit or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 11:46
S55	13613	(measur\$5 or determin\$3 or obtain\$3 or calculat\$3 or estimat\$3 or monitor\$3) near4 temperature with (die or chip or IC or integrated adj circuit or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 11:47

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S56	113	S53 and S55	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 13:40
S57	2020	(measur\$5 or determin\$3 or obtain\$3 or calculat\$3 or estimat\$3 or monitor\$3) with (power near4 consum\$5) with (die or chip or IC or integrated adj circuit or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 13:40
S58	13613	(measur\$5 or determin\$3 or obtain\$3 or calculat\$3 or estimat\$3 or monitor\$3) near4 temperature with (die or chip or IC or integrated adj circuit or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/17 09:21
S59	113	S57 and S58	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 13:41
S60	58	S59 and voltage with temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 13:41
S61	524	(power near4 consum\$5) and (ambient near3 temperature) and (junction near5 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR .	OFF	2006/05/16 14:52
S62	596	(power near4 consum\$5) and (ambient near3 temperature) and (junction near5 temperature) and (IC or integrated adj circuit or die or wafer or chip or substrate or CPU or processor or device or UUT or DUT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 14:54
S63	25	(power near4 consum\$5) same (ambient near3 temperature) same (junction near5 temperature) same (IC or integrated adj circuit or die or wafer or chip or substrate or CPU or processor or device or UUT or DUT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 15:04
S64	18	S63 and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/16 15:04
S65	74	(determin\$3 or calculat\$3 or estimat\$3 or comput\$3) near4 junction adj temperature same (die or chip or IC or integrated adj circuit or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 10:58

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S66	20	S65 and (power or current) same (ambient near3 temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/17 09:23
S67	9	body near5 voltage near5 bias\$3 same (junction near3 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 11:07
S68	2	("6100751").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/24 09:47
S69	6	body near5 voltage near5 bias\$3 same (junction adj temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/24 10:12
S70	94	("6002620" "4997366" "5313085" "5349559" "5426616" "5512353" "5523619" "5770504" "5798281" "5817543" "5847591" "5867421" "6014052" "6091287" "6141245" "6243283" "6288561" "6323663" "6838896" "6891387" "20030151421" "20040222809" "5408951" "5694048" "5938427" "6109767" "6175241" "5532612" "4495622" "4514786" "4992849" "4992850" "5196785" "5234149" "5440240" "5530376" "5572140" "5585282" "5705933" "5781022" "5789794" "5808947" "5861660" "5883008" "5954832" RE36325 "6221682" "6221682" "4281449" "4288911").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 10:50
S71	785	324/760.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 13:01
S72 .	943	324/755.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 13:00
S73	4917	324/765.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:01

S74	4523	324/754.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:01
S75	3416	714/724.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:02
S76	858	438/15.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR ·	OFF	2006/10/25 13:02
S77	3488	365/201.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/25 13:01
S78	1	(determin\$3 or calculat\$3 or estimat\$3 or comput\$3) same temperature same (die or chip or IC or integrated adj circuit or wafer) same (power or current) same (ambient near3 temperature) same body same voltage same bias\$3 same (junction near3 temperature).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/25 12:58
S79	1	(body near5 voltage near5 bias\$3 same (junction near3 temperature)).clm.	US-PGPUB	OR	ON	2006/10/25 11:08
S80	1	(integrated adj circuit same voltage with bias\$3 same (junction near3 temperature)).clm.	US-PGPUB	OR	ON	2006/10/25 11:09